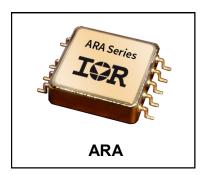


HIGH RELIABILITY RADIATION HARDENED LOW POWER DC-DC CONVERTER

100V Input, 5W Single/Dual Output



Description

The ARA100 Series of DC-DC converters are low power radiation hardened, high reliability devices designed for radiation environments such as those encountered by geostationary earth orbit satellites, deep space probes and communication systems. Features include small size, high efficiency, low weight and a high tolerance to total ionizing dose, single event effects and environmental stresses such as temperature extremes, mechanical shock, and vibration. Extensive documentation including Radiation test reports, Thermal Analysis, Stress Analysis and MTBF are available.

The ARA100 Series converters incorporate a fixed frequency flyback topology with magnetic feedback. All models include an external inhibit port. They are encased in a hermetic 1.20" x 1.20" x 0.31" AlSi package and weigh less than 15 grams. The package utilizes rugged ceramic feed-through copper core pins and is hermetically sealed using laser welding.

Environmental screening includes temperature cycling, constant acceleration, fine and gross leak, and burn-in as specified by MIL-PRF-38534 for class K hybrids.

Non-flight versions of the ARA100 Series converters are available for system development purposes. Variations in electrical specifications and screening to meet custom requirements can be accommodated.

Features

- Total Dose Guaranteed to 100 kRads (Si)
- SEE with LET up to 82 MeV·cm²/mg
- Low Weight < 15 grams
- Magnetically Coupled Feedback
- 65V to 120V DC Input Range
- Up to 5W Output Power
- Single and Dual Output Models Include 3.3, 5, 6, 12, 15, ±5, ±12 and ±15V
- Low Quiescent Current
- High Efficiency to 80%
- -55°C to +85°C Operating Temperature Range
- 100MΩ @ 200V DC Isolation
- Under-Voltage Lockout
- Short Circuit and Overload Protection
- External Inhibit
- Output Adjustment (For both Single and Dual Output Models)
- Remote Sense (For Single Output Models only)

Applications

- Geostationary Earth Orbit Satellites (GEO)
- Deep Space Satellites / Probes
- Strategic Weapons and Communication System

Circuit Description

The ARA100 Series converters utilize a flyback topology with a nominal switching frequency of 400 kHz. Electrical isolation and tight output regulation are achieved through the use of a magnetically coupled feedback.

Output current is limited under any load fault condition to approximately 165% of rated. The converter will resume normal operation when the load current is reduced below the current limit point. This protects the converter from both overload and short circuit conditions. There are no latching elements included in the load fault protection circuits to eliminate the possibility of falsely triggering the protection circuits during single event radiation exposure.

An under-voltage lockout circuit prohibits the converter from operating when the line voltage is too low to maintain the output voltage. The converter will not start until the line voltage rises to approximately 59 volts and will shut down when the input voltage drops below 57 volts. The hysteresis reduces the possibility of line noise interfering with the converter's start-up and shut down circuitry.

An external inhibit port is provided to control converter operation. The converters's operation is inhibited when this pin is pulled low. It is intended to be driven by an open collector device. The pin may be left open for normal operation and has a nominal open circuit voltage of about 12.75V.

Design Methodology

The ARA Series was developed using a proven conservative design methodology, which includes selecting radiation tolerant, and established reliability components and fully de-rating to the requirements of MIL-STD-975, MIL-STD-1547, and NASA EE-INST-002. Conservative de-rating of the radiation-hardened power MOSFET virtually eliminates the possibility of SEGR and SEB. A magnetic feedback circuit is utilized instead of opto-couplers to minimize temperature, radiation and aging sensitivity. PSPICE was used extensively to predict and optimize circuit performance for both beginning and end-of-life. Thorough design analyses include Radiation Susceptibility, Worst Case, Stress, Thermal, Failure Modes and Effects (FMEA) and Reliability (MTBF).



Specifications

Absolute Maximum Ratings		Recommended Operating Conditions		
Input Voltage	-0.5Vdc to +120Vdc	Input Voltage	+65Vdc to +110Vdc	
Output power	Internally limited	Output power	0 to Max. Rated	
Lead Temperature	+300°C for 10 seconds			
Operating temperature	-55°C to +125°C	Operating temperature	-55°C to +85°C	
Storage temperature	-55°C to +135°C	Operating temperature ¹	-55°C to +70°C	

Meets de-rating per MIL-STD-975, MIL-STD-1547, NASA EEE-INST-002 when Vin nominal is 100V and Vin worst case is 110V. (Note 13)

Electrical Performance Characteristics : BOL (Beginning of Life)

		Conditions		Limits		
Parameter	Group A Subgroup			Nom.	Max.	Unit
Input Voltage (V _{IN})			65	100	110	V
Output Voltage (V _{OUT}) ARA10003R3S ARA10005S ARA10006S ARA10012S ARA10015S ARA10005D ARA10012D	1,2,3 1,2,3 1,2,3 1,2,3 1,2,3 1,2,3 1,2,3	I _{OUT} = 100% rated load Note 4	3.27 4.95 5.94 11.88 14.85 ±4.95 ±11.88	3.30 5.00 6.00 12.00 15.00 ±5.00 ±12.00	3.33 5.05 6.06 12.12 15.15 ±5.05 ±12.12	V
ARA 100 12D ARA 100 15D	1,2,3		±11.00	±12.00	±12.12	
Output power (P _{OUT}) ARA10003R3S All others Output current (I _{OUT}) ARA10003R3S ARA10005S	1,2,3	V _{IN} = 65, 100, 110 Volts, Note 2 V _{IN} = 65, 100, 110 Volts, Note 2	0 0 0		4.0 5.0 1.21 1.0	W
ARA10006S ARA10012S ARA10015S ARA10005D ARA10012D ARA10015D	1,2,3	Either Output, Note 3 Either Output, Note 3 Either Output, Note 3	0 0 0 0 0		0.83 0.416 0.333 0.8 0.33 0.27	Α
Line regulation (VR _{LINE})	1,2,3	V _{IN} = 65, 100, 110 Volts I _{OUT} = 0, 50%, 100% rated, Notes 1, 4	-0.50		0.50	%
Load regulation (VR _{LOAD})	1,2,3	I _{OUT} = 0, 50%, 100% rated, Notes 1, 4 V _{IN} = 65, 100, 110 Volts	-1.0		1.0	%
Total regulation (Line and Load)	1,2,3	V _{IN} = 65, 100, 110 Volts I _{OUT} = 0, 50%, 100% rated, Dual Model is measured from + Output to -Output, Note 14	-1.0		1.0	%

For Notes to Electrical Performance Characteristics, refer to page 5



Electrical Performance Characteristics (continued)

		Conditions	Limits				
Parameter	Group A Subgroup	$-55^{\circ}C \le T_C \le +85^{\circ}C$ $V_{IN} = 100V DC \pm 5\%, C_L = 0uF$ unless otherwise specified	Min.	Nom.	Max.	. Unit	
Cross regulation (VR _{CROSS}) ARA10005D ARA10012D ARA10015D	1,2,3	Duals only, Note 5 V _{IN} = 65, 100, 110 Volts	-3.5 -3.0 -2.5		3.5 3.0 2.5	%	
Input current (I _{IN})	1,2,3	I _{OUT} = 0, Pin 4 open Pin 4 shorted to Pin 2			8.0 1.5	mA	
Switching frequency (F _S)	1,2,3		350	400	475	kHz	
Output ripple (V _{RIP}) ARA10003R3S ARA10005S ARA10006S ARA10012S ARA10015S ARA10005D ARA10012D ARA10015D	1,2,3	V _{IN} = 65, 100, 110 Volts I _{OUT} = 100% rated load Notes 4, 6			35 50 50 50 50 50 50 50	mVp-p	
Efficiency (E _{FF}) ARA10003R3S ARA10005S ARA10006S ARA10012S ARA10015S ARA10005D ARA10012D ARA10015D	1,2,3	I _{OUT} = 100% rated load Note 4	65 71 71 75 75 73 74 74	71 75 75 79 80 75 77 78		%	
Enable Input (Inhibit Function) Open circuit voltage Drive current (sink) Voltage range	1,2,3	Note 1	11 -0.7		14 800 50	V µA V	
Current Limit Point Expressed as a percentage of full rated load current	1,2,3	V _{OUT} = 90% of Nominal, Note 4	105		200	%	
Power dissipation, load fault (P _D)	1,2,3	Short Circuit, Overload, Note 8			3.0	W	
Under Voltage Threshold Release (On) Lockout (OFF) Hysteresis (UVR-UVLO)	1,2,3		51 0.5		61	V	
Output response to step load changes (V _{TLD})	4,5,6	Half Load to/ from Full Load, Notes 4,9	-300		300	mVpk	
Recovery time, step load changes (T _{TLD})	4,5,6	Half Load to/from Full Load, Notes 4, 9,10			200	μs	
Output response to step line changes (VT _{LN})	4,5,6	65V to/from 110V I _{OUT} =100% rated load, Notes 1, 4,11	-300		300	mVpk	
Recovery time, step line changes (T _{TLN})	4,5,6	65V to/from 110V I _{OUT} =100% rated load, Notes 1,4,10,11			200	μs	

For Notes to Electrical Performance Characteristics, refer to page 5



Electrical Performance Characteristics (continued)

Parameter	Group A	-55°C ≤ 1°C ≤ +85°C		≤ T _C ≤ +85°C		
T drameter	Subgroup	V_{IN} = 100V DC ± 5%, C_L = 0 uF unless otherwise specified	Min	Nom	Max	Unit
Turn-on Response Overshoot (V _{OS}) Turn-on Delay (T _{DLY})	4,5,6	No Load, Full Load Notes 4,12	1.5		500 10	mV ms
Capacitive Load (C _L) ARA10003R3S ARA10005S ARA10006S ARA10012S ARA10015S ARA10005D ARA10012D ARA10015D	1	I _{OUT} = 100% rated load No effect on DC performance Notes 1, 4, 7 Each output on duals			1000 700 500 100 80 300 90 60	μF
Line Rejection	1	I _{OUT} = 100% rated load DC to 50 kHz, Notes 1, 4		50		dB
Isolation	1	Input to Output or Any Pin to Case except Pin 1, test @ 200VDC	100			МΩ
Device Weight					15	g
MTBF		MIL-HDBK-217F2, SF, 35°C	8.0 x 10 ⁶			Hours

Notes: Electrical Performance Characteristics

- 1. Parameter is tested as part of design characterization or after design changes. Thereafter, parameter shall be guaranteed to the limits specified.
- 2. Parameter verified during line and load regulation tests.
- 3. Output load current must be distributed such that at least 20% of the total load current is being provided by one of the outputs.
- 4. Load current split equally between outputs on dual output models.
- 5. Cross regulation is measured with 20% rated load on output under test while changing the load on the other output from 20% to 80% of rated.
- 6. Guaranteed for a D.C. to 20 MHz bandwidth. Tested using a 20 kHz to 10 MHz bandwidth.
- 7. Capacitive load may be any value from 0 to the maximum limit without compromising dc performance.
- 8. Overload power dissipation is defined as the device power dissipation with the load set such that $V_{OUT} = 90\%$ of nominal.
- 9. Load step transition time \geq 10 μ s.
- 10 Recovery time is measured from the initiation of the transient to where V_{OUT} has returned to within ±1% of its steady state value.
- 11. Line step transition time \geq 100 μ s.
- 12. Turn-on delay time from either a step application of input power or a logic low to a logic high transition on the inhibit pin (Pin 4) to the point where V_{OUT} = 90% of nominal.
- 13. For ceramic capacitors with voltage stress less than 10V, derating requirements require minimum 100V rated capacitors. The product will use capacitors with a minimum rating of 16V.
- 14. Total regulation is +/- 3% for end of life.

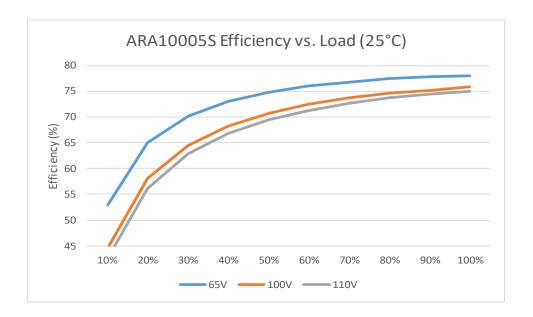
Radiation Performance Characteristics

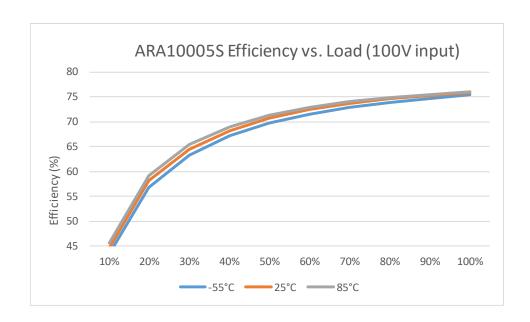
Test	Conditions		Тур	Max	Unit
Total Ionizing Dose (TID) (Gamma)	T _C = 25°C, Dose Rate = 14 - 50 Rads/s (Si) Operating bias applied during exposure, Half Rated Load, V _{IN} = 100V	100		150	kRrads (Si)
Single Event Effects (SEE) SEU, SEL, SEGR, SEB - Note 1	Heavy Ions (LET) Operating bias applied during exposure, Full Rated Load, V _{IN} = 65V, 100V, 110V - Note 2	82			MeV·cm²/mg

Notes:

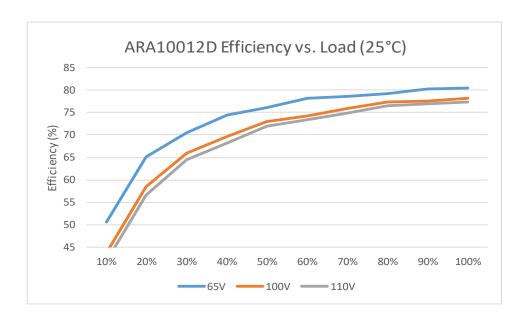
- 1. Output perturbation is less than + 5% / -8% of nominal output voltage.
- 2. Beam condition: Min LET = 82 MeV.cm²/mg

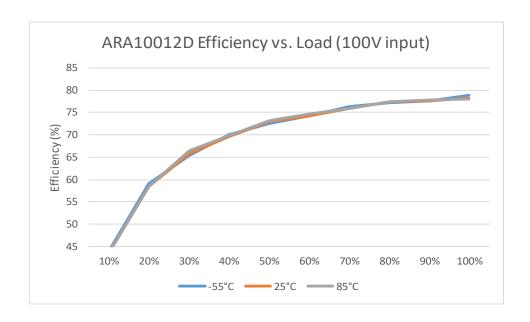
Efficiency Curves:



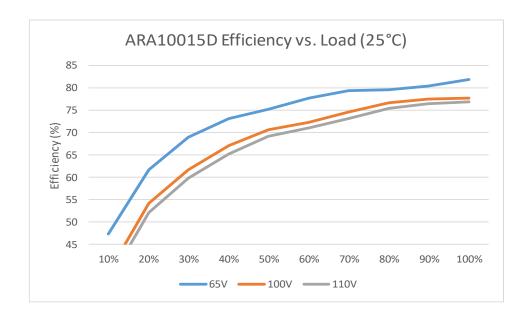


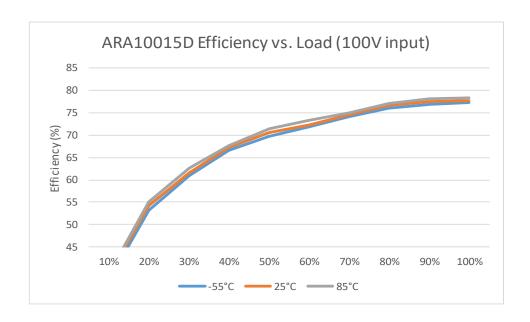
Efficiency Curves:





Efficiency Curves:





ARA Series Input Ripple Current:

In the ARA Series converters, as shown in the Block diagrams (page 10), there is no series inductor before the input capacitor. Therefore, when measuring the input ripple current it is dependent on the series impedance between the power source and the converter input. For input ripple current measurements, a set-up with a known inductor value and a large capacitor connected between the power source and an ARA converter should be used. The capacitor is used to minimize the source impedance supplying the converter. A ripple current is measured with a current probe connected between the converter and the large capacitor. In order to reduce the input ripple current, the AF100461 filter may be used between the source voltage and the ARA Series converters.

ARA Series Output Voltage Adjustment:

Output of ARA Series can be adjusted to be greater or less than the nominal output voltage with an external resistor. However, the ranges of the output voltages are limited depending on the model as specified in Table 1 and 2. An approximate value of the resistor can be determined using the following formula.

For Single Output Model: Radj = [A - (B x Vout)] / [(C x Vout) - D]
For Dual Output Model: Radj = [A - (B x 2Vout)] / [(C x 2Vout) - D]

Where:

Radj is the value of the external resistor in ohms and is connected as specified in Table 1 and 2. Power rating of the resistor shall be $\geq 0.125W$. A Metal film resistor with temperature coefficient a of $\leq \pm 50$ ppm and tolerance of $\leq 1\%$ is recommended. However, the final selection is dependent on specific design requirements.

Vout is the desired output voltage in volts.

A, B, C, and D are unique constants depending on the model as shown in Table 1 for Single Output models and Table 2 for Dual Output models.

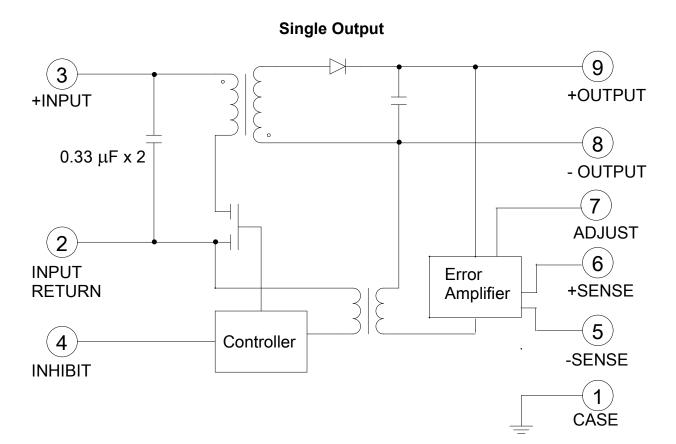
Table 1: Single Output Voltage Ranges, Constants and Resistor connection by Model

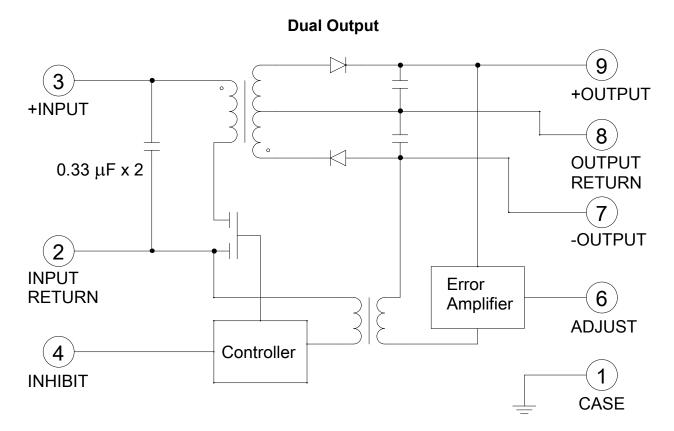
Model	Output Voltage Range	Radj connection between	А	В	С	D
ARA10003R3S	3.3 to 3.6	Pin 7 & Pin 5	122.4E+6	12.0E+6	10.0E+3	33.3E+3
ARA10005S	5.0 to 5.5	Pin 7 & Pin 5	1.8E+9	300.0E+6	10.0E+3	50.0E+3
ARA 100055	4.5 to 5.5	Pin 7 & Pin 6	700.0E+6	160.0E+6	4.0E+3	20.0E+3
ARA10012S	12.0 to 13.2	Pin 7 & Pin 5	4.8E+9	315.0E+6	10.5E+3	126.3E+3
ARA 100 123	10.8 to 12.0	Pin 7 & Pin 6	1.9E+9	294.0E+6	4.2E+3	50.5E+3
ARA10015S	15.0 to 16.5	Pin 7 & Pin 5	5.8E+9	300.0E+6	10.0E+3	150.0E+3
	13.5 to 15.0	Pin 7 & Pin 6	2.3E+9	320.0E+6	4.0E+3	60.0E+3

Table 2: Dual Output Voltage Ranges, Constants and Resistor connection by Model

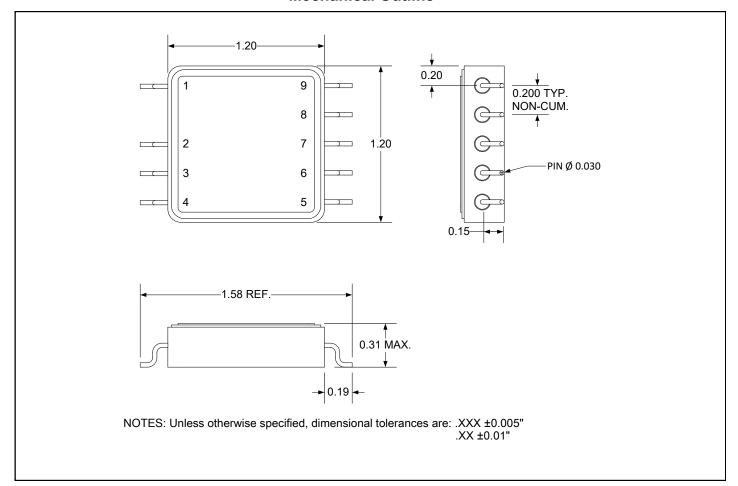
Model	Output Voltage Range	Radj connection between	А	В	С	D
ARA10005D	5.0 to 5.5	Pin 6 & Pin 7	3.8E+9	300.0E+6	10.0E+3	100.0E+3
ARA 10005D	4.5 to 5.5	Pin 6 & Pin 9	1.5E+9	240.0E+6	4.0E+3	40.0E+3
ARA10012D	12.0 to 13.2	Pin 6 & Pin 7	9.4E+9	300.0E+6	10.0E+3	240.0E+3
ARA 100 12D	10.8 to 12.0	Pin 6 & Pin 9	3.7E+9	464.0E+6	4.0E+3	96.0E+3
ARA10015D	15.0 to 16.5	Pin 6 & Pin 7	11.8E+9	300.0E+6	10.0E+3	300.0E+3
ARA 100 15D	13.5 to 15.0	Pin 6 & Pin 9	4.7E+9	560.0E+6	4.0E+3	120.0E+3

Block Diagrams





Mechanical Outline



Pin Designation Tables *

Single Output

Pin#	Designation			
1	Case Ground			
2	Input Return			
3	+ Input			
4	Inhibit			
5	- Sense			
6	+ Sense			
7	Adjust			
8	- Output			
9	+ Output			

Dual Output

Pin#	Designation			
1	Case Ground			
2	Input Return			
3	+ Input			
4	Inhibit			
5	NC			
6	Adjust			
7	- Output			
8	Output Return			
9	+ Output			

^{*} Pin Designations are subject to change



Device Screening

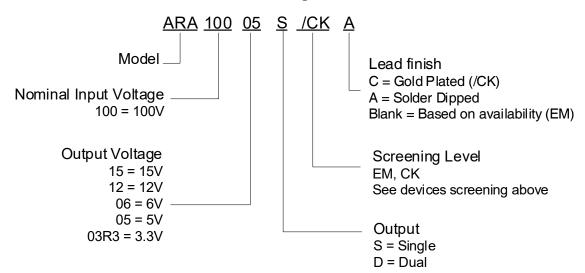
Part Number Designator		/ EM ①	/CK ②
Compliance Level	MIL-PRF-38534	_	K level compliant
Certification Mark		_	СК
Screening Requirement	MIL-STD-883 Method	_	_
Temperature Range	_	Room Temperature	-55°C to +85°C
Element Evaluation	MIL-PRF-38534	N/A	Class K
Non-Destructive Bond Pull	2023	N/A	Yes
Internal Visual	2017	IR Defined	Yes
Temperature Cycle	1010	N/A	Cond C
Constant Acceleration	2001, Y1 Axis	N/A	3000 Gs
PIND	2020	N/A	Cond A
Burn-In	1015	N/A	320 hrs @ 125°C (2 x 160 hrs)
Final Electrical (Group A)	MIL-PRF-38534 & Specification	Room Temperature	-55°C, +25°C, +85°C
PDA	MIL-PRF-38534	N/A	2%
Seal, Fine and Gross	1014	N/A	Cond CH
Radiographic	2012	N/A	Yes
External Visual	2009	IR Defined	Yes

Notes:

- "EM" grade parts are strictly intended to permit the customer to determine the electrical functionality of the device in the customer's application in ambient conditions. The use of EM devices in production applications presents an unquantifiable risk of failure and IR HiRel disclaims all responsibility for such failure.
- © "CK" grade is the flight model (FM) compliant to K Level screening as defined in the DLA Land and Maritime MIL-PRF-38534 requirements, but is not necessarily a DLA Land and Maritime qualified SMD per MIL-PRF-38534. The governing document for this part number designator is the IR HiRel datasheet (this document). Radiation rating as stated in the "Radiation Performance Characteristics" section, is verified by analysis and test per IR HiRel internal procedure. The part is marked with the IR base part number and the "CK" certification mark.



Part Numbering





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Data and specifications subject to change without notice.



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